



COPY OF PAPERS
ORIGINALLY FILED

#10/Amdt A
15.29/5629
6/29/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

TSUGANE et al.

Serial No. 09/759,666

Filed: January 13, 2001

For: SEMICONDUCTOR DEVICES AND METHODS
FOR MANUFACTURING THE SAME

Group Art Unit: 2813

Examiner: Schillinger, L.

RECEIVED
JUN 19 2002
TECHNOLOGY CENTER 2800

AMENDMENT

Assistant Commissioner for Patents
Washington, DC 20231

Dear Sirs:

In response to the Office Action dated December 5, 2001, the response being due by June 5, 2002 by the enclosed Petition for Extension of Time, please enter and consider the following.

IN THE CLAIMS:

Please cancel claims 9-14 without prejudice.

Please amend claim 16 as follows:

16. (amended)

A method according to claim 15, further comprising, prior to forming the storage node of the cell capacitor and the lower electrode of the capacitor element, forming an additional conducting layer and etching the additional conducting layer to form a word line that is a component of the DRAM and to form a connection layer that is located in a common layer of the word line and that is configured to electrically connect the lower electrode to another element in the semiconductor device.